

CLAIMS

1. A polishing pad having a polishing region and a light-transmitting region used in chemical mechanical polishing, wherein the light-transmitting region satisfies that the difference
5 ΔT ($\Delta T = T_0 - T_1$) (%) between T_0 and T_1 is within 10 (%) over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is the light transmittance (%) of the light-transmitting region measured at the measurement wavelength λ after dipping in a KOH aqueous solution at pH 11 for 24 hours and T_0 is the
10 light-transmittance (%) measured at the measurement wavelength λ before the dipping.

2. A polishing pad having a polishing region and a light-transmitting region used in chemical mechanical polishing,
15 wherein the light-transmitting region satisfies that the difference ΔT ($\Delta T = T_0 - T_1$) (%) between T_0 and T_1 is within 10 (%) over the whole range of measurement wavelengths of from 400 to 700 nm, wherein T_1 is the light transmittance (%) of the light-transmitting region measured at the measurement wavelength λ after dipping in
20 an H_2O_2 aqueous solution at pH 4 for 24 hours and T_0 is the light-transmittance (%) measured at the measurement wavelength λ before the dipping.

3. The polishing pad according to claim 1 or 2, wherein the
25 material forming the light-transmitting region is non-foam.

**4. The polishing pad according to any of claims 1 to 3,
wherein the material forming the polishing region is fine-cell foam.**

5 **5. The polishing pad according to any of claims 1 to 4,
wherein the light-transmitting region at the polishing side does not
have an uneven structure retaining and renewing an abrasive
liquid.**

10 **6. The polishing pad according to any of claims 1 to 5,
wherein the polishing region at the polishing side is provided with
grooves.**

15 **7. A method of manufacturing a semiconductor device,
which comprises a step of polishing the surface of a semiconductor
wafer with the polishing pad according to any of claims 1 to 6.**